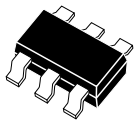
CMXD2004

SUPER-MINI
TRIPLE ISOLATED
SURFACE MOUNT
HIGH VOLTAGE
SWITCHING DIODE



SOT-26 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD2004 type contains three (3) Isolated High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high voltage capability. Marking code is X04.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, tp=1 ms	I_{FSM}	4000	mA
Forward Surge Current, tp=1 s	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	V_R=240V		100	nA
I_R	V_R=240V, T_A=150°C		100	μA
BV_R	I_R=100μA	300		V
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1 MHz		5.0	pF
t_{rr}	I_F=I_R=30mA, Rec. To 3.0mA, R_L=100Ω		50	ns

R1 (14-Sept 2000)

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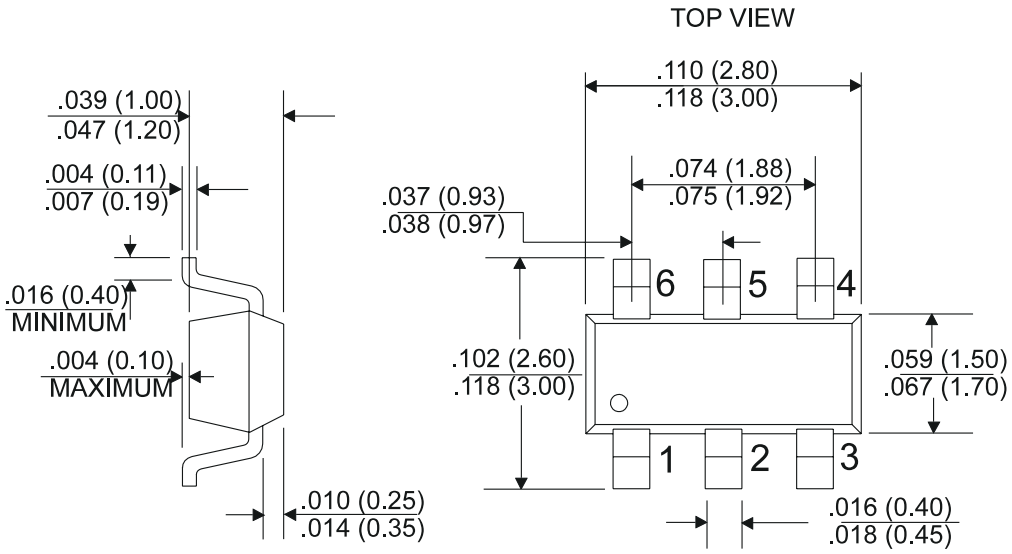
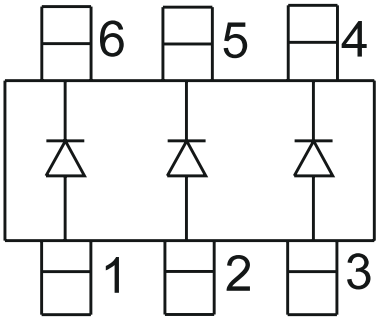
MECHANICAL OUTLINE - SOT-26 CASE



All Dimensions in Inches (mm)

Pin Configuration



Lead Code

1) Anode 1
2) Anode 2
3) Anode 3
4) Cathode 3
5) Cathode 2
6) Cathode 1

R1 (14-Sept 2000)